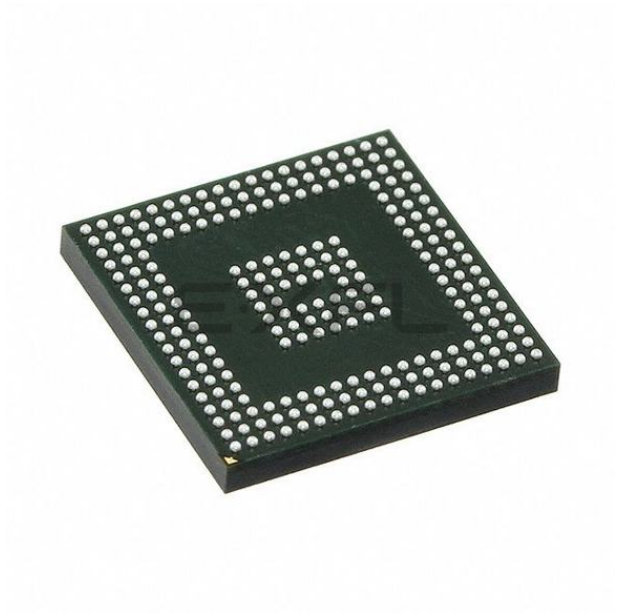

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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	4075
Number of Logic Elements/Cells	52160
Total RAM Bits	2764800
Number of I/O	106
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	238-LFBGA, CSPBGA
Supplier Device Package	238-CSBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7a50t-1cpg236i

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies (6)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies (6)	–	+260	°C
T_j	Maximum junction temperature(6)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide*.
4. The maximum limit applied to DC signals.
5. For maximum undershoot and overshoot AC specifications, see Table 4.
6. For soldering guidelines and thermal considerations, see UG475: *7 Series FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}	Internal supply voltage	0.95	1.00	1.05	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCBRAM}	Block RAM supply voltage	0.95	1.00	1.05	V
V_{CCO}(3)(4)	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
V_{IN}(5)	I/O input voltage	–0.20	–	V_{CCO} + 0.20	V
	I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V
I_{IN}(6)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}(7)	Battery voltage	1.0	–	1.89	V
GTP Transceiver					
$V_{MGTAVCC}$(8)(9)	Analog supply voltage for the GTP transmitter and receiver circuits	0.97	1.0	1.03	V
$V_{MGTAVTT}$(8)(9)	Analog supply voltage for the GTP transmitter and receiver termination circuits	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system consult UG483, *7 Series FPGAs PCB Design and Pin Planning Guide*.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG482: *7 Series FPGAs GTP Transceiver User Guide*.
9. Voltages are specified for the temperature range of T_j = 0°C to +85°C.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}(2)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}(3)	Battery supply current	–	–	150	nA
R_{IN_TERM}(4)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40) for commercial (C), and industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50) for commercial (C), and industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60) for commercial (C), and industrial (I), and extended (E) temperature devices	44	60	83	Ω

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{CCO}/2$ level.

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks[1]**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.40	100	–0.40	100
V_{CCO} + 0.45	100	–0.45	61.7
V_{CCO} + 0.50	100	–0.50	25.8
V_{CCO} + 0.55	100	–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7A100T	155	155	155	108	mA
		XC7A200T	328	328	328	232	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7A100T	4	4	4	4	mA
		XC7A200T	5	5	5	5	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7A100T	36	36	36	36	mA
		XC7A200T	73	73	73	73	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7A100T	4	4	4	4	mA
		XC7A200T	11	11	11	11	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperature (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTP transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels(1)(2)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 5	Note 5
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.500	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. For detailed interface specific DC voltage levels, see UG471: *7 Series FPGAs SelectIO Resources User Guide*.

LVDS DC Specifications (LVDS_25)

See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information on the LVDS_25 standard in the HR I/O banks.

Table 11: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.375	2.500	2.625	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.300	1.200	1.425	V

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in v1.07 from the 14.4/2012.4 device pack for ISE® Design Suite14.4 and Vivado® Design Suite 2012.4 for the -3, -2, -2L (1.0V), and -1 speed grades and v1.05 from the 14.4/2012.4 device pack for the -2L (0.9V) speed grade.

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Artix-7 FPGAs.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Artix-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the AC Switching Characteristics, page 9.

Table 14: **Networking Applications Interface Performances**

Description	Speed Grade				Units
	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	680	680	600	600	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	1250	1250	950	950	Mb/s
SDR LVDS receiver (SFI-4.1)(1)	680	680	600	600	Mb/s
DDR LVDS receiver (SPI-4.2)(1)	1250	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 15: **Maximum Physical Interface (PHY) Rate for Memory Interfaces(1)(2)**

Memory Standard	Speed Grade				Units
	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	
4:1 Memory Controllers					
DDR3	1066	800	800	800	Mb/s
DDR3L	800	800	667	667	Mb/s
DDR2	800	800	667	667	Mb/s
LPDDR2	667	667	533	533	Mb/s
2:1 Memory Controllers					
DDR3	800	700	620	620	Mb/s
DDR3L	800	700	620	620	Mb/s
DDR2	800	700	620	620	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).

IOB Pad Input/Output/3-State

Table 16 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 16: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.26	1.34	1.41	1.58	3.80	3.93	4.18	4.41	4.37	4.59	5.01	5.06	ns
LVTTL_S8	1.26	1.34	1.41	1.58	3.54	3.66	3.92	4.15	4.11	4.32	4.75	4.80	ns
LVTTL_S12	1.26	1.34	1.41	1.58	3.52	3.65	3.90	4.13	4.09	4.31	4.73	4.78	ns
LVTTL_S16	1.26	1.34	1.41	1.58	3.07	3.19	3.45	3.68	3.64	3.85	4.28	4.33	ns
LVTTL_S24	1.26	1.34	1.41	1.58	3.29	3.41	3.67	3.90	3.86	4.07	4.50	4.55	ns
LVTTL_F4	1.26	1.34	1.41	1.58	3.26	3.38	3.64	3.86	3.83	4.04	4.46	4.51	ns
LVTTL_F8	1.26	1.34	1.41	1.58	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns
LVTTL_F12	1.26	1.34	1.41	1.58	2.73	2.85	3.10	3.33	3.29	3.51	3.93	3.98	ns
LVTTL_F16	1.26	1.34	1.41	1.58	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns
LVTTL_F24	1.26	1.34	1.41	1.58	2.52	2.65	2.90	3.22	3.09	3.31	3.73	3.87	ns
LVDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns
MINI_LVDS_25	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns
BLVDS_25	0.73	0.81	0.88	0.90	1.84	1.96	2.21	2.44	2.40	2.62	3.04	3.09	ns
RSDS_25 (point to point)	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns
PPDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.88	1.86	2.07	2.49	2.53	ns
TMDS_33	0.73	0.81	0.88	0.90	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns
PCI33_3	1.24	1.32	1.39	1.57	3.10	3.22	3.48	3.71	3.67	3.88	4.31	4.36	ns
HSUL_12	0.67	0.75	0.82	0.87	1.80	1.93	2.18	2.41	2.37	2.59	3.01	3.06	ns
DIFF_HSUL_12	0.68	0.76	0.83	0.88	1.80	1.93	2.18	2.21	2.37	2.59	3.01	2.86	ns
HSTL_I_S	0.67	0.75	0.82	0.87	1.62	1.74	1.99	2.19	2.19	2.40	2.82	2.84	ns
HSTL_II_S	0.65	0.73	0.80	0.85	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns
HSTL_I_18_S	0.67	0.75	0.82	0.87	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns
HSTL_II_18_S	0.66	0.75	0.81	0.87	1.41	1.54	1.79	1.97	1.98	2.20	2.62	2.62	ns
DIFF_HSTL_I_S	0.68	0.76	0.83	0.85	1.59	1.71	1.96	2.13	2.15	2.37	2.79	2.78	ns
DIFF_HSTL_II_S	0.68	0.76	0.83	0.85	1.51	1.63	1.88	2.07	2.08	2.29	2.71	2.72	ns
DIFF_HSTL_I_18_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.96	1.95	2.17	2.59	2.61	ns
DIFF_HSTL_II_18_S	0.70	0.78	0.85	0.87	1.46	1.58	1.84	2.00	2.03	2.24	2.67	2.65	ns
HSTL_I_F	0.67	0.75	0.82	0.87	1.10	1.22	1.48	1.69	1.67	1.88	2.31	2.34	ns

Table 23: **IO_FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T_{OFFCKO_DO}	RDCLK to Q outputs	0.55	0.60	0.68	0.81	ns
T_{CKO_FLAGS}	Clock to IO_FIFO flags	0.55	0.61	0.77	0.55	ns
Setup/Hold						
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK	0.47/0.02	0.51/0.02	0.58/0.02	0.76/–0.05	ns
$T_{IFFCCK\_WREN}/T_{IFFCKC\_WREN}$	WREN to WRCLK	0.42/–0.01	0.47/–0.01	0.53/–0.01	0.70/–0.05	ns
$T_{OFFCCK\_RDEN}/T_{OFFCKC\_RDEN}$	RDEN to RDCLK	0.53/0.02	0.58/0.02	0.66/0.02	0.79/–0.02	ns
Minimum Pulse Width						
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK	1.62	2.15	2.15	2.15	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK	1.62	2.15	2.15	2.15	ns
Maximum Frequency						
F_{MAX}	RDCLK and WRCLK	266.67	200.00	200.00	200.00	MHz

CLB Switching Characteristics

Table 24: **CLB Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Combinatorial Delays						
T_{ILO}	An – Dn LUT address to A	0.10	0.11	0.13	0.15	ns, Max
T_{ILO_2}	An – Dn LUT address to AMUX/CMUX	0.27	0.30	0.36	0.41	ns, Max
T_{ILO_3}	An – Dn LUT address to BMUX_A	0.42	0.46	0.55	0.65	ns, Max
T_{ITO}	An – Dn inputs to A – D Q outputs	0.94	1.05	1.27	1.51	ns, Max
T_{AXA}	AX inputs to AMUX output	0.62	0.69	0.84	1.01	ns, Max
T_{AXB}	AX inputs to BMUX output	0.58	0.66	0.83	0.98	ns, Max
T_{AXC}	AX inputs to CMUX output	0.60	0.68	0.82	0.98	ns, Max
T_{AXD}	AX inputs to DMUX output	0.68	0.75	0.90	1.08	ns, Max
T_{BXB}	BX inputs to BMUX output	0.51	0.57	0.69	0.82	ns, Max
T_{BXD}	BX inputs to DMUX output	0.62	0.69	0.82	0.99	ns, Max
T_{CXC}	CX inputs to CMUX output	0.42	0.48	0.58	0.69	ns, Max
T_{CXD}	CX inputs to DMUX output	0.53	0.59	0.71	0.86	ns, Max
T_{DXD}	DX inputs to DMUX output	0.52	0.58	0.70	0.84	ns, Max
Sequential Delays						
T_{CKO}	Clock to AQ – DQ outputs	0.40	0.44	0.53	0.62	ns, Max
T_{SHCKO}	Clock to AMUX – DMUX outputs	0.47	0.53	0.66	0.73	ns, Max
Setup and Hold Times of CLB Flip-Flops Before/After Clock CLK						
T_{AS}/T_{AH}	A_N – D_N input to CLK on A – D flip-flops	0.07/0.12	0.09/0.14	0.11/0.18	0.11/0.20	ns, Min
T_{DICK}/T_{CKDI}	A_X – D_X input to CLK on A – D flip-flops	0.06/0.19	0.07/0.21	0.09/0.26	0.09/0.31	ns, Min
	A_X – D_X input through MUXs and/or carry logic to CLK on A – D flip-flops	0.59/0.08	0.66/0.09	0.81/0.11	0.97/0.12	ns, Min
$T_{CECK\_CLB}/T_{CKCE\_CLB}$	CE input to CLK on A – D flip-flops	0.15/0.00	0.17/0.00	0.21/0.01	0.34/–0.01	ns, Min
T_{SRCK}/T_{CKSR}	SR input to CLK on A – D flip-flops	0.38/0.03	0.43/0.04	0.53/0.05	0.62/0.05	ns, Min
Set/Reset						
T_{SRMIN}	SR input minimum pulse width	0.52	0.78	1.04	0.95	ns, Min
T_{RQ}	Delay from SR input to AQ – DQ flip-flops	0.53	0.59	0.71	0.83	ns, Max
T_{CEO}	Delay from CE input to AQ – DQ flip-flops	0.52	0.58	0.70	0.83	ns, Max
F_{TOG}	Toggle frequency (for export control)	1412	1286	1098	1098	MHz

Table 32: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BHCKO_O}	BUFH delay from I to O	0.10	0.11	0.13	0.16	ns
$T_{BHCCK\_CE}/T_{BHCKC\_CE}$	CE pin setup and hold	0.19/0.13	0.22/0.15	0.28/0.21	0.35/0.08	ns
Maximum Frequency						
F_{MAX_BUFH}	Horizontal clock buffer (BUFH)	628.00	628.00	464.00	394.00	MHz

Table 33: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
T_{DCD_CLK}	Global clock tree duty-cycle distortion(1)	All	0.20	0.20	0.20	0.25	ns
T_{CKSKEW}	Global clock tree skew(2)	XC7A100T	0.27	0.33	0.36	0.48	ns
		XC7A200T	0.40	0.48	0.54	0.69	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion	All	0.14	0.14	0.14	0.14	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region	All	0.03	0.03	0.03	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion	All	0.18	0.18	0.18	0.18	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the I/O flip flops. For all I/O standards, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx FPGA_Editor and Timing Analyzer tools to evaluate clock skew specific to your application.

MMCM Switching Characteristics

Table 34: **MMCM Specification**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
MMCM_F_{INMAX}	Maximum input clock frequency	800.00	800.00	800.00	800.00	MHz
MMCM_F_{INMIN}	Minimum input clock frequency	10.00	10.00	10.00	10.00	MHz
MMCM_$F_{INJITTER}$	Maximum input clock period jitter	< 20% of clock input period or 1 ns Max				
MMCM_F_{INDUTY}	Allowable input duty cycle: 10—49 MHz	25	25	25	25	%
	Allowable input duty cycle: 50—199 MHz	30	30	30	30	%
	Allowable input duty cycle: 200—399 MHz	35	35	35	35	%
	Allowable input duty cycle: 400—499 MHz	40	40	40	40	%
	Allowable input duty cycle: >500 MHz	45	45	45	45	%
MMCM_F_{MIN_PSCLK}	Minimum dynamic phase-shift clock frequency	0.01	0.01	0.01	0.01	MHz
MMCM_F_{MAX_PSCLK}	Maximum dynamic phase-shift clock frequency	550.00	500.00	450.00	450.00	MHz
MMCM_F_{VCOMIN}	Minimum MMCM VCO frequency	600.00	600.00	600.00	600.00	MHz
MMCM_F_{VCOMAX}	Maximum MMCM VCO frequency	1600.00	1440.00	1200.00	1200.00	MHz

Table 34: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical(1)	1.00	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical(1)	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs(2)	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter	Note 3				
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty-cycle precision(4)	0.20	0.20	0.20	0.25	ns
$MMCM\_T_{LOCKMAX}$	MMCM maximum lock time	100.00	100.00	100.00	100.00	µs
$MMCM\_F_{OUTMAX}$	MMCM maximum output frequency	800.00	800.00	800.00	800.00	MHz
$MMCM\_F_{OUTMIN}$	MMCM minimum output frequency(5)(6)	4.69	4.69	4.69	4.69	MHz
$MMCM\_T_{EXTFDVAR}$	External clock feedback variation	< 20% of clock input period or 1 ns Max				
$MMCM\_RST_{MINPULSE}$	Minimum reset pulse width	5.00	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum frequency at the phase frequency detector	550.00	500.00	450.00	450.00	MHz
$MMCM\_F_{PFDMIN}$	Minimum frequency at the phase frequency detector	10.00	10.00	10.00	10.00	MHz
$MMCM\_T_{FBDELAY}$	Maximum delay in the feedback path	3 ns Max or one CLKIN cycle				
MMCM Switching Characteristics Setup and Hold						
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and hold of phase-shift enable	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and hold of phase-shift increment/decrement	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase shift clock-to-out of PSDONE	0.59	0.68	0.81	0.78	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK						
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR setup/hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI setup/hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN setup/hold	1.76/0.00	1.97/0.00	2.29/0.00	2.40/0.00	ns, Min
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE setup/hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY	0.65	0.72	0.99	0.70	ns, Max
F_{DCK}	DCLK frequency	200.00	200.00	200.00	100.00	MHz, Max

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard. See http://www.xilinx.com/products/intellectual-property/clocking_wizard.htm.
4. Includes global clock buffer.
5. Calculated as $F_{VCO}/128$ assuming output duty cycle is 50%.
6. When CLKOUT4_CASCADE = TRUE, $MMCM\_F_{OUTMIN}$ is 0.036 MHz.

Table 48 summarizes the DC specifications of the clock input of the GTP transceiver. Consult UG482: *7 Series FPGAs GTP Transceiver User Guide* for further details.

Table 48: **GTP Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	350	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	100	–	nF

GTP Transceiver Switching Characteristics

Consult UG482: *7 Series FPGAs GTP Transceiver User Guide* for further information.

Table 49: **GTP Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade								Units
			1.0V						0.9V		
			-3		-2/-2L		-1		-2L		
			Package Type								
			FFG FBG SBG	FGG FTG CSG	FFG FBG SBG	FGG FTG CSG	FFG FBG SBG	FGG FTG CSG	FFG FBG SBG	FGG FTG CSG	
F_{GTPMAX}	Maximum GTP transceiver data rate		6.6	5.4	6.6	5.4	3.75	3.75	3.75	3.75	Gb/s
F_{GTPMIN}	Minimum GTP transceiver data rate		0.500	0.500	0.500	0.500	0.500	0.500	0.500	0.500	Gb/s
$F_{GTPRANGE}$	PLL line rate range	1	3.2–6.6		3.2–6.6		3.2–3.75		3.2–3.75		Gb/s
		2	1.6–3.3		1.6–3.3		1.6–3.2		1.6–3.2		Gb/s
		4	0.8–1.65		0.8–1.65		0.8–1.6		0.8–1.6		Gb/s
		8	0.5–0.825		0.5–0.825		0.5–0.8		0.5–0.8		Gb/s
$F_{GTPPLLRANGE}$	GTP transceiver PLL frequency range		1.6–3.3		1.6–3.3		1.6–3.3		1.6–3.3		GHz

Table 50: **GTP Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$F_{GTPDRPCLK}$	GTPDRPCLK maximum frequency	175	175	156	125	MHz

Table 51: **GTP Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range		60	–	660	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	20% – 80%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	40	–	60	%

GTP Transceiver Protocol Jitter Characteristics

For Table 56 through Table 60, the UG482: *7 Series FPGAs GTP Transceiver User Guide* contains recommended settings for optimal usage of protocol specific characteristics.

Table 56: **Gigabit Ethernet Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 57: **XAUI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 58: **PCI Express Protocol Characteristics(1)**

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation					
PCI Express Gen 1	Total transmitter jitter	2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter	5000	–	0.25	UI
PCI Express Receiver High Frequency Jitter Tolerance					
PCI Express Gen 1	Total receiver jitter tolerance	2500	0.65	–	UI
PCI Express Gen 2(2)	Receiver inherent timing error	5000	0.40	–	UI
	Receiver inherent deterministic timing error		0.30	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. Using common REFCLK.

Table 59: **CEI-6G Protocol Characteristics**

Description	Line Rate (Mb/s)	Interface	Min	Max	Units
CEI-6G Transmitter Jitter Generation					
Total transmitter jitter(1)	4976–6375	CEI-6G-SR	–	0.3	UI
CEI-6G Receiver High Frequency Jitter Tolerance					
Total receiver jitter tolerance(1)	4976–6375	CEI-6G-SR	0.6	–	UI

Notes:

1. Tested at most commonly used line rate of 6250 Mb/s using 390.625 MHz reference clock.

Table 60: **CPRI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
CPRI Transmitter Jitter Generation				
Total transmitter jitter	614.4	–	0.35	UI
	1228.8	–	0.35	UI
	2457.6	–	0.35	UI
	3072.0	–	0.35	UI
	4915.2	–	0.3	UI
	6144.0	–	0.3	UI
CPRI Receiver Frequency Jitter Tolerance				
Total receiver jitter tolerance	614.4	0.65	–	UI
	1228.8	0.65	–	UI
	2457.6	0.65	–	UI
	3072.0	0.65	–	UI
	4915.2(1)	0.60	–	UI
	6144.0(1)	0.60	–	UI

Notes:

1. Tested to CEI-6G-SR.

Integrated Interface Block for PCI Express Designs Switching Characteristics

More information and documentation on solutions for PCI Express designs can be found at:
http://www.xilinx.com/technology/protocols/pciexpress.htm

Table 61: **Maximum Performance for PCI Express Designs**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$F_{PIPECLK}$	Pipe clock maximum frequency	250.00	250.00	250.00	250.00	MHz
$F_{USERCLK}$	User clock maximum frequency	250.00	250.00	250.00	250.00	MHz
$F_{USERCLK2}$	User clock 2 maximum frequency	250.00	250.00	250.00	250.00	MHz
F_{DRPCLK}	DRP clock maximum frequency	250.00	250.00	250.00	250.00	MHz

Table 62: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
DCLK Duty Cycle			40	–	60	%
XADC Reference(5)						
External Reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-Chip Reference		Ground V_{REFP} pin to AGND, T_j = –40°C to 100°C	1.2375	1.25	1.2625	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for BitGen option XADCEnhancedLinearity = ON.
3. See the ADC chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
4. See the Timing chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted. On-chip reference variation is ±1%.

Configuration Switching Characteristics

Table 63: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Power-up Timing Characteristics						
T_{PL}(1)	Program latency	5.00	5.00	5.00	5.00	ms, Max
T_{POR}(1)	Power-on reset (50 ms ramp rate time)	10/50	10/50	10/50	10/50	ms, Min/Max
	Power-on reset (1 ms ramp rate time)	10/35	10/35	10/35	10/35	ms, Min/Max
$T_{PROGRAM}$	Program pulse width	250.00	250.00	250.00	250.00	ns, Min
CCLK Output (Master Mode)						
T_{ICCK}	Master CCLK output delay	150.00	150.00	150.00	150.00	ns, Min
T_{MCCKL}	Master CCLK clock Low time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
T_{MCCKH}	Master CCLK clock High time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
F_{MCCK}	Master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
	Master CCLK frequency for AES encrypted x16	50.00	50.00	50.00	35.00	MHz, Max
F_{MCCK_START}	Master CCLK frequency at start of configuration	3.00	3.00	3.00	3.00	MHz, Typ
$F_{MCCKTOL}$	Frequency tolerance, master mode with respect to nominal CCLK	±50	±50	±50	±50	%, Max
CCLK Input (Slave Modes)						
T_{SCCKL}	Slave CCLK clock minimum Low time	2.50	2.50	2.50	2.50	ns, Min
T_{SCCKH}	Slave CCLK clock minimum High time	2.50	2.50	2.50	2.50	ns, Min
F_{SCCK}	Slave CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
EMCCLK Input (Master Mode)						
T_{EMCCKL}	External master CCLK Low time	2.50	2.50	2.50	2.50	ns, Min
T_{EMCCKH}	External master CCLK High time	2.50	2.50	2.50	2.50	ns, Min
F_{EMCCK}	External master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max

Table 63: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Internal Configuration Access Port						
F_{ICAPCK}	Internal configuration access port (ICAPE2) clock frequency	100.00	100.00	100.00	70.00	MHz, Max
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B setup/hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T_{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F_{RBCCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup/hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Flash Master Mode Programming Switching						
T_{BPICCO} (2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Flash Master Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] setup/hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T_{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
$T_{SPICCFC}$	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in UG470: *7 Series FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 64 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 64: **eFUSE Programming Conditions** (1)

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

Revision History

The following table shows the revision history for this document:

Date	Version	Description
09/26/11	1.0	Initial Xilinx release.
11/07/11	1.1	Revised the V_{OCM} specification in Table 11. Updated the AC Switching Characteristics based upon the ISE 13.3 software v1.02 speed specification throughout document including Table 12 and Table 13. Added MMCM_$T_{FBDELAY}$ while adding MMCM_ to the symbol names of a few specifications in Table 34 and PLL to the symbol names in Table 35. In Table 36 through Table 43, updated the pin-to-pin description with the SSTL15 standard. Updated units in Table 46.
02/13/12	1.2	Updated the Artix-7 family of devices listed throughout the entire data sheet. Updated the AC Switching Characteristics based upon the ISE 13.4 software v1.03 for the -3, -2, and -1 speed grades and v1.00 for the -2L speed grade. Updated summary description on page 1. In Table 2, revised V_{CCO} for the 3.3V HR I/O banks and updated T_j. Updated the notes in Table 5. Added MGTAVCC and MGTAVTT power supply ramp times to Table 7. Rearranged Table 8, added Mobile_DDR, HSTL_I_18, HSTL_II_18, HSUL_12, SSTL135_R, SSTL15_R, and SSTL12 and removed DIFF_SSTL135, DIFF_SSTL18_I, DIFF_SSTL18_II, DIFF_HSTL_I, and DIFF_HSTL_II. Added Table 9 and Table 10. Revised the specifications in Table 11. Revised V_{IN} in Table 47. Updated the eFUSE Programming Conditions section and removed the endurance table. Added the table. Revised F_{TXIN} and F_{RXIN} in Table 53. Revised I_{CCADC} and updated Note 1 in Table 62. Revised DDR LVDS transmitter data width in Table 14. Removed notes from Table 24 as they are no longer applicable. Updated specifications in Table 63. Updated Note 1 in Table 33.
06/01/12	1.3	Reorganized entire data sheet including adding Table 40 and Table 44. Updated T_{SOL} in Table 1. Updated I_{BATT} and added R_{IN_TERM} to Table 3. Updated Power-On/Off Power Supply Sequencing section with regards to GTP transceivers. In Table 8, updated many parameters including SSTL135 and SSTL135_R. Removed V_{OX} column and added DIFF_HSUL_12 to Table 10. Updated V_{OL} in Table 11. Updated Table 14 and removed notes 2 and 3. Updated Table 15. Updated the AC Switching Characteristics based upon the ISE 14.1 software v1.03 for the -3, -2, -2L (1.0V), -1, and v1.01 for the -2L (0.9V) speed specifications throughout the document. In Table 27, updated Reset Delays section including Note 10 and Note 11. In Table 53, replaced F_{TXOUT} with F_{GLK}. Updated many of the XADC specifications in Table 62 and added Note 2. Updated and moved *Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK* section from Table 63 to Table 34 and Table 35.

Date	Version	Description
09/20/12	1.4	In Table 1, updated the descriptions, changed V_{IN} and Note 2, and added Note 4. In Table 2, changed descriptions and notes. Updated parameters in Table 3. Added Table 4. Revised the Power-On/Off Power Supply Sequencing section. Updated standards and specifications in Table 8, Table 9, and Table 10. Removed the XC7A350T device from data sheet. Updated the AC Switching Characteristics section to the ISE 14.2 speed specifications throughout the document. Updated the IOB Pad Input/Output/3-State discussion and changed Table 17 by adding $T_{IOIBUFDISABLE}$. Removed many of the combinatorial delay specifications and T_{CINCK}/T_{CKCIN} from Table 24.Changed F_{PFDMAX} conditions in Table 34 and Table 35. Updated the GTP Transceiver Specifications section, moved the GTP Transceiver DC characteristics section to the overall DC Characteristics section, and added the GTP Transceiver Protocol Jitter Characteristics section. In Table 62, updated Note 1. In Table 63, updated T_{POR}.
02/01/13	1.5	Updated the AC Switching Characteristics based upon the 14.4/2012.4 device pack for ISE 14.4 and Vivado 2012.4, both at v1.07 for the -3, -2, -2L (1.0V), -1 speed specifications, and v1.05 for the -2L (0.9V) speed specifications throughout the document. Production changes to Table 12 and Table 13 for -3, -2, -2L (1.0V), -1 speed specifications. Revised I_{DCIN} and I_{DCOUT} and added Note 5 in Table 1. Added Note 2 to Table 2. Updated Table 5. Added minimum current specifications to Table 6. Removed SSTL12 and HSTL_I_12 from Table 8. Removed DIFF_SSTL12 from Table 10. Updated Table 12. Added a 2:1 memory controller section to Table 15. Updated Note 1 in Table 31. Revised Table 33. Updated Note 1 and Note 2 in Table 46. Updated D_{VPPIN} in Table 47. Updated V_{IDIFF} in Table 48. Removed T_{LOCK} and T_{PHASE} and revised F_{GCLK} in Table 51. Updated T_{DLOCK} in Table 52. Updated Table 53. In Table 54, updated T_{RTX}, T_{FTX}, $V_{TXOOBVDPP}$, and revised Note 1 through Note 7. In Table 55, updated RX_{SST} and RX_{PPMTOL} and revised Note 4 through Note 7. In Table 60, revised and added Note 1. Revised the maximum external channel input ranges in Table 62. In Table 63, revised F_{MCCK} and added the Internal Configuration Access Port section.

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